

## L810N-66-60

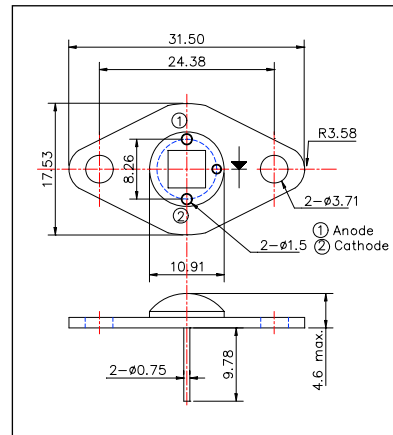
### Epoxy Lens Type Infrared Illuminator

L810N-66-60 is a wide viewing and extremely high output power illuminator assembled with a total of 60 high efficiency AlGaAs diode chips, mounted on a metal stem TO-66 with AlN ceramics and covered with epoxy resin. These devices are designed for high current operation with proper heat sinking to improve thermal conductive efficiency.

<Specifications>

1. Product Name: IR Illuminator
2. Type Number: L810N-66-60
3. Chip:
  - Chip material: AlGaAs
  - Peak Wavelength: 810nm typ.
  - Dimension: 400um x 400um
  - Number: 60pcs
4. Package
  - Type: TO-66 Stem Cu made
  - Insulator: AlN Ceramics
  - Lens: Clear Silicone and Epoxy Lens

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Power Dissipation	PD	9.5	W
Forward Current	IF	1000	mA
Pulse Forward Current*	IFP	6000	mA
Reverse Voltage	VR	50	V
Junction Temperature	Tj	100	°C
Thermal Resistance**	Rthjp	5	K/W
Operating Temperature	TOPR	-30 ~ +80	°C
Storage Temperature	TSTG	-30 ~+110	°C
Soldering Temperature***	TSOL	265	°C

\* Duty=1% and Pulse Width=10us

\*\* Junction - metal block

\*\*\* Soldering condition must be completed within 3 second at 265°C.

Electro-Optical Characteristics						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Radiated Power	PO	IF=600mA		800		mW
		IF=1A,tp=1ms		1300		
Radiant Intensity	IE	IF=600mA		310		mW/sr
		IF=1A,tp=1ms		500		
Forward Voltage	VF	IF=600mA		8.0		V
		IF=1A,tp=1ms		8.4		
Peak Wavelength	λP	IF=600mA		810		nm
Half Width	Δλ	IF=600mA		35		nm
Viewing Half Angle	θ1/2	IF=600mA		±60		deg
Rise Time	Tr	IF=600mA		100		ns
Fall Time	tf	IF=600mA		100		ns

Heat sink is required by 2K/W